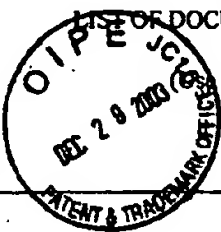
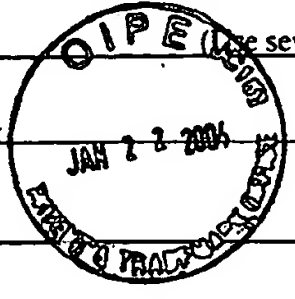


FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number 5308-156		Serial No. 09/911,995	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)				Applicants: Ryu et al.			
				Filing Date: July 24, 2001		Group: 2811	
U. S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
27K/27	1.	5,587,870	12/24/96	Anderson et al.	361	313	
	2.	5,877,045	3/2/99	Kapoor	438	151	
	3.	6,136,728	10/24/00	Wang	438	773	
	4.	6,063,698	05/16/00	Tseng et al.	438	585	
	5.	6,048,766	04/11/00	Gardner et al.	438	257	
27K/27	6.	6,028,012	02/22/00	Wang	438	779	

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U. S. PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
JCH	1	5,479,316	12/26/95	Smrtic et al.	361	322	
	2	5,739,564	04/14/98	Kosa et al.	257	298	
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	4	6,239,463	05/29/01	Williams et al.	257	328	
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JCH 8	WO98/02924	01/22/98	PCT				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
JCH 9	Dimitrijevic et al., "Nitridation of Silicon-Dioxide Films Grown on 6H Silicon Carbide", <i>IEEE Electronic Device Letters</i> , Vol. 18, No. 5, May 05, 1997, pp. 175-177.						
10	De Mao et al., "Thermal Oxidation of SiC in N ₂ O", <i>J. Electrochem. Soc.</i> , Vol. 141, 1994, pp. L150-L152.						
11	Ryu et al., Article and Presentation: "27 mΩ-cm ² , 1.6 kV Power DiMOSFETs in 4H-SiC," <i>Proceedings of the 14 International Symposium on Power Semiconductor Devices & ICs 2002</i> , June 4-7, 2002, Santa Fe, NM.						
12	Kobayashi et al. "Dielectric Breakdown and Current Conduction of Oxide/Nitride/Oxide Multi-Layer Structures," <i>1990 IEEE Symposium on VLSI Technology</i> . pp. 119-120.						
JCH 13	Ma et al. "Fixed and trapped charges at oxide-nitride-oxide heterostructure interfaces formed by remote plasma enhanced chemical vapor deposition," <i>J. Vac. Sci. Technol. B</i> . Vol. 11, No. 4, Jul/Aug 1993, pp. 1533-40.						

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 DATE CONSIDERED 3 March 2003

Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.